

# MSKSEMI

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Product data sheet

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SOD-123FL

## FEATURES

- \* Ideal for surface mount applications
- \* Easy pick and place
- \* Built-in strain relief
- \* Fast switching speed

## MECHANICAL DATA

- \* Case: Molded plastic
- \* Epoxy: UL 94V-0 rate flame retardant
- \* Metallurgically bonded construction
- \* Polarity: Color band denotes cathode end
- \* Mounting position: Any

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature unless otherwise specified.  
Single phase half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

TYPE NUMBER	F1A	F1B	F1D	F1G	F1J	F1K	F1M	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at Ta=25°C	1.0							A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	30							A
Maximum Instantaneous Forward Voltage at 1.0A	1.3							V
Maximum DC Reverse Current Ta=25°C	5.0							µA
at Rated DC Blocking Voltage Ta=100°C	100							µA
Maximum Reverse Recovery Time (Note 1)	150			250		500		nS
Typical Junction Capacitance (Note 2)	15							pF
Typical Thermal Resistance R JA (Note 3)	80							°C/W
Operating and Storage Temperature Range Tj, Tstg	-65 — +150							°C
Marking Code								

**NOTES:**

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
3. Thermal Resistance from Junction to Ambient.

FIG.1-TYPICAL FORWARD CHARACTERISTICS

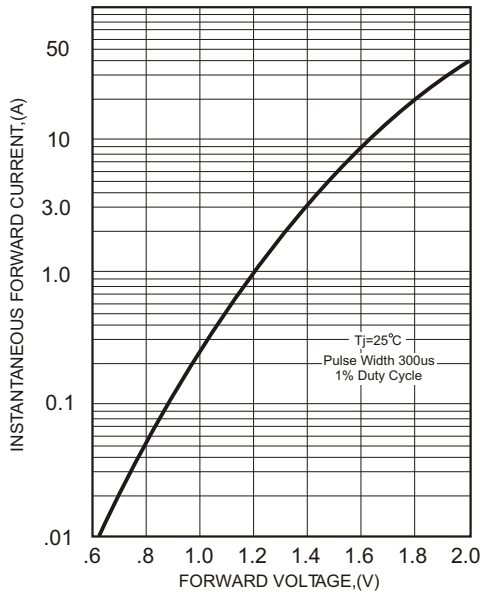


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

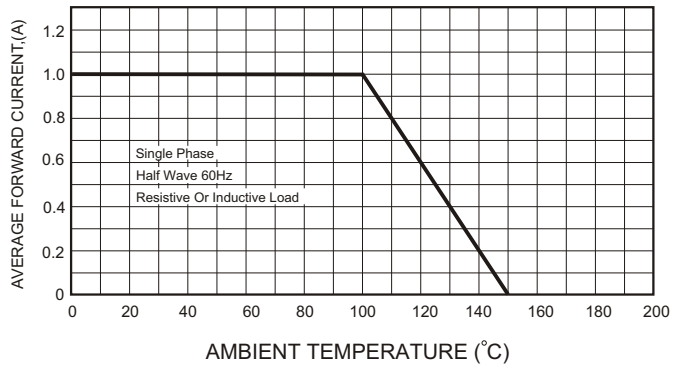
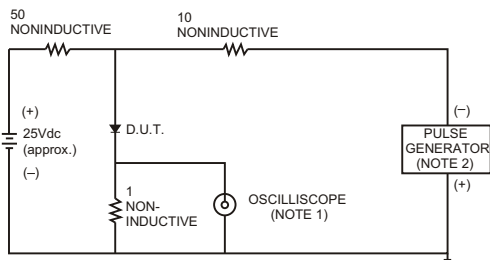


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm, 22pF.  
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

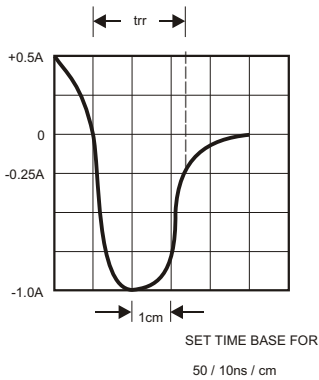


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

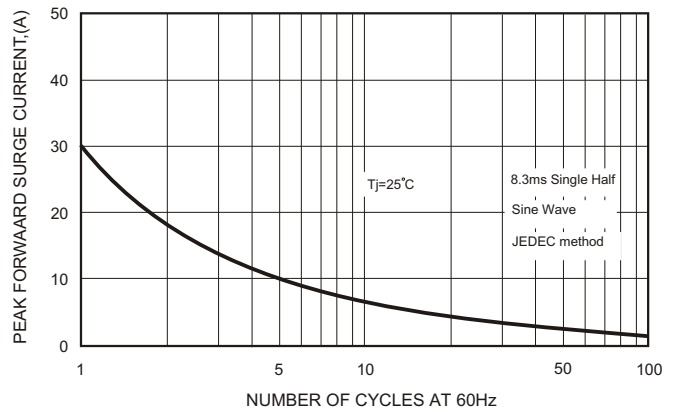
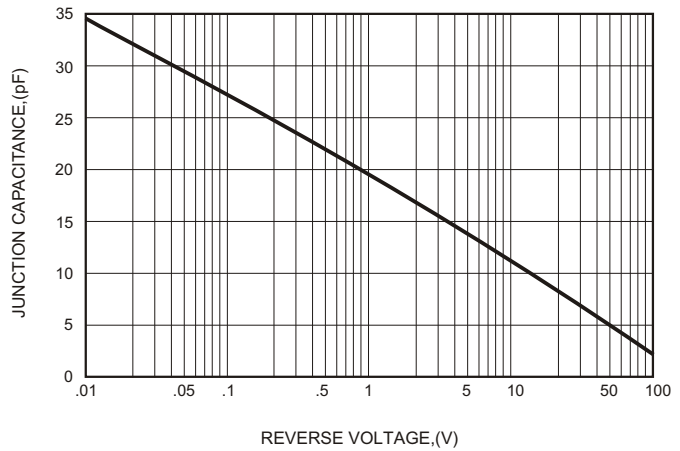
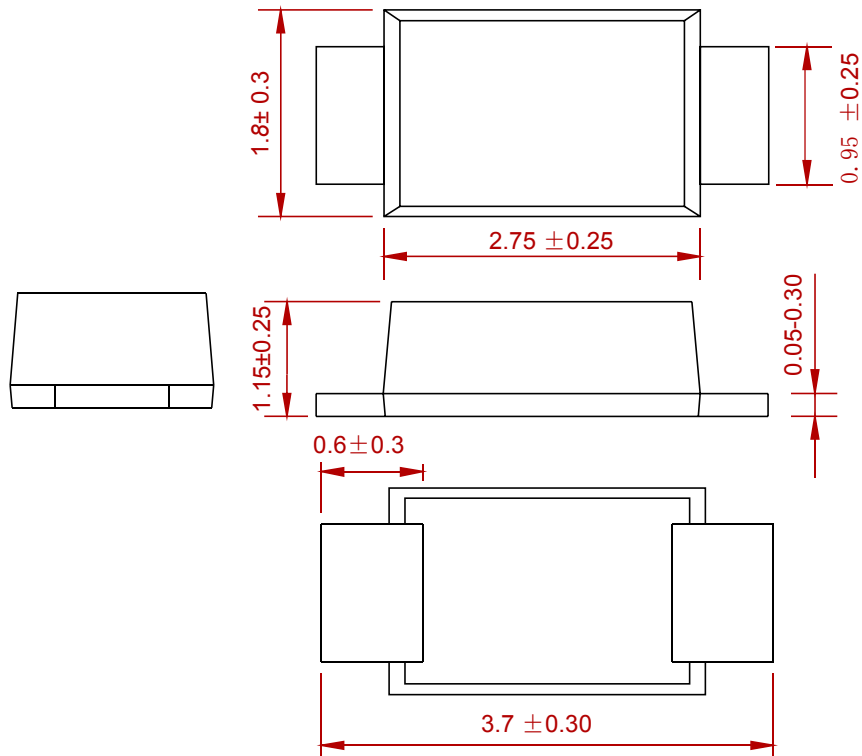


FIG.5-TYPICAL JUNCTION CAPACITANCE

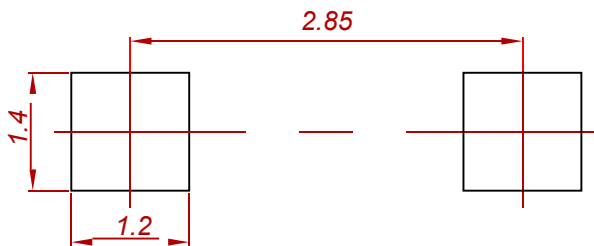


**PACKAGE MECHANICAL DATA**



*Dimensions in millimeters*

**Suggested Pad Layout**



**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$  mm.
3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

P/N	PKG	QTY
F1A THRU F1M	SOD-123FL	3000

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